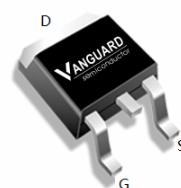


## Features

- N-Channel
- Enhancement mode
- Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5$  V
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant; Hg-Free

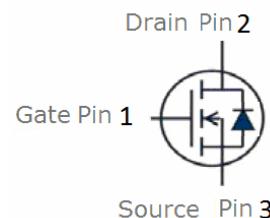
$V_{DS}$	40	V
$R_{DS(on),TYP}$ @ $V_{GS}=10$ V	36	mΩ
$R_{DS(on),TYP}$ @ $V_{GS}=4.5$ V	42	mΩ
$I_D$	20	A

TO-252



Halogen-Free

Part ID	Package Type	Marking	Tape and reel information
VSD040N04MS	TO-252	040N04M	2500pcs/reel



## Maximum ratings, at $T_j=25$ °C, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	40	V
$I_s$	Diode continuous forward current	$T_c=25$ °C	A
$I_D$	Continuous drain current@ $V_{GS}=10$ V	$T_c=25$ °C	A
		$T_c=100$ °C	A
$I_{DM}$	Pulse drain current tested ①	$T_c=25$ °C	A
$P_d$	Maximum power dissipation	$T_c=25$ °C	W
$V_{GS}$	Gate-Source voltage	$\pm 20$	V
$T_{STG}$	Storage temperature range	-55 to 175	°C
$T_j$	Maximum Junction Temperature	175	°C
EAS	Avalanche energy, single pulsed ②	$I_D=8$ A	mJ

## Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	5.0	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	70	°C/W

### Typical Electrical Characteristics

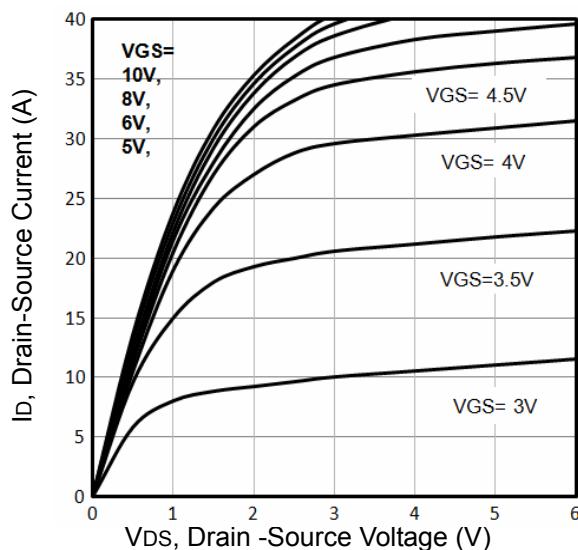
Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	40	--	--	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current( $T_c=25^\circ\text{C}$ )	$V_{\text{DS}}=32\text{V}$ , $V_{\text{GS}}=0\text{V}$	--	0.01	1	$\mu\text{A}$
	Zero Gate Voltage Drain Current( $T_c=125^\circ\text{C}$ )	$V_{\text{DS}}=32\text{V}$ , $V_{\text{GS}}=0\text{V}$	--	5	100	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	--	--	$\pm 100$	nA
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_D=250\mu\text{A}$	1.0	2.0	3.0	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance <sup>①</sup>	$V_{\text{GS}}=10\text{V}$ , $I_D=10\text{A}$	--	36	40	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance <sup>①</sup>	$V_{\text{GS}}=4.5\text{V}$ , $I_D=5\text{A}$	--	42	50	$\text{m}\Omega$
<b>Dynamic Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	--	345	--	pF
$C_{\text{oss}}$	Output Capacitance		--	43	--	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	18	--	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=20\text{V}$ , $I_D=5\text{A}$ , $V_{\text{GS}}=10\text{V}$	--	8.6	--	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	1.7	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	2.2	--	nC
<b>Switching Characteristics</b>						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=20\text{V}$ , $I_D=1\text{A}$ , $R_G=6.8\Omega$ , $V_{\text{GS}}=10\text{V}$	--	5.8	--	nS
$t_r$	Turn-on Rise Time		--	2.8	--	nS
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	16	--	nS
$t_f$	Turn-Off Fall Time		--	2.2	--	nS
<b>Source- Drain Diode Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$I_{\text{SD}}$	Source-drain current(Body Diode)	$T_c=25^\circ\text{C}$	--	--	20	A
$V_{\text{SD}}$	Forward on voltage	$I_{\text{SD}}=2\text{A}$ , $V_{\text{GS}}=0\text{V}$	--	0.78	1.3	V
$t_{\text{rr}}$	Reverse Recovery Time	$T_j=25^\circ\text{C}$ , $I_{\text{sd}}=5\text{A}$ , $V_{\text{GS}}=0\text{V}$ $di/dt=100\text{A}/\mu\text{s}$	--	25	--	nS
$Q_{\text{rr}}$	Reverse Recovery Charge		--	28	--	nC

NOTE:

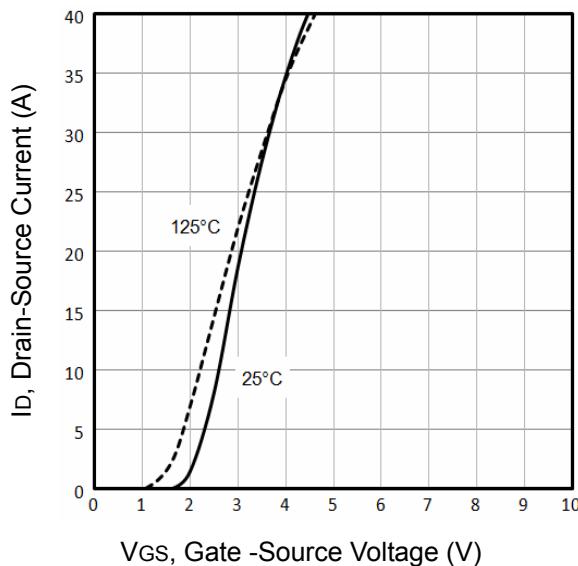
①Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

② Limited by  $T_{J\text{max}}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.1\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 8\text{A}$ ,  $V_{GS} = 10\text{V}$ . Part not recommended for use above this value.

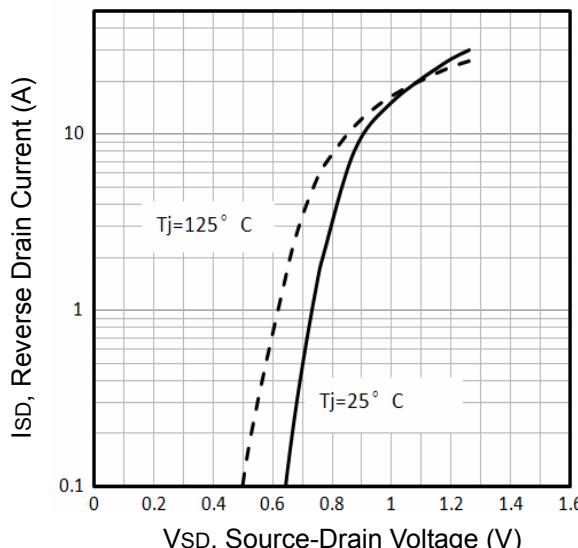
### Typical Characteristics



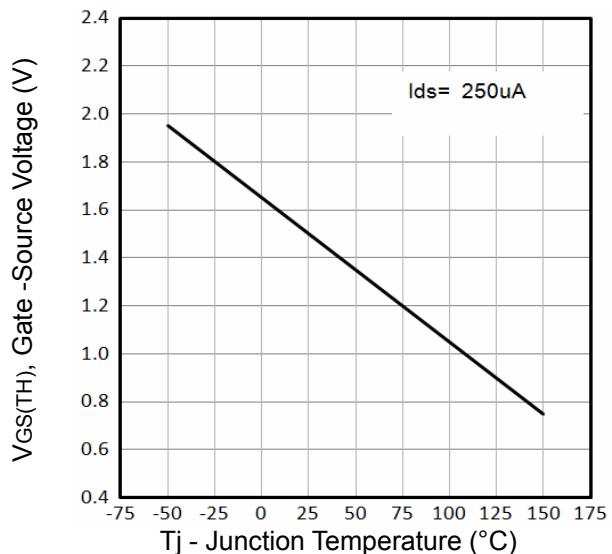
**Fig1.** Typical Output Characteristics



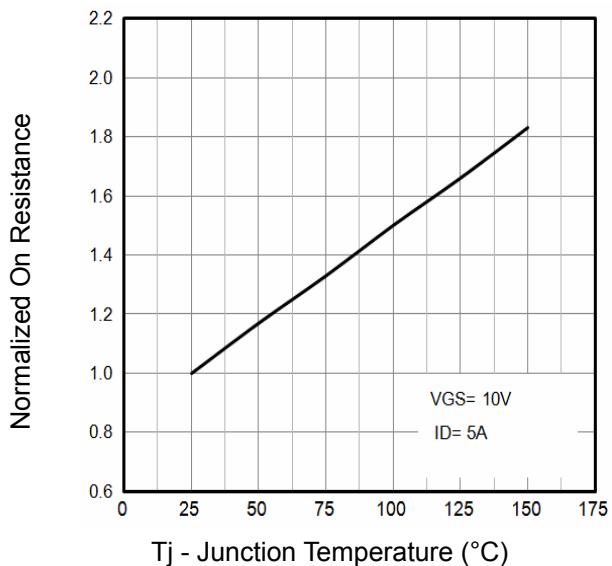
**Fig3.** Typical Transfer Characteristics



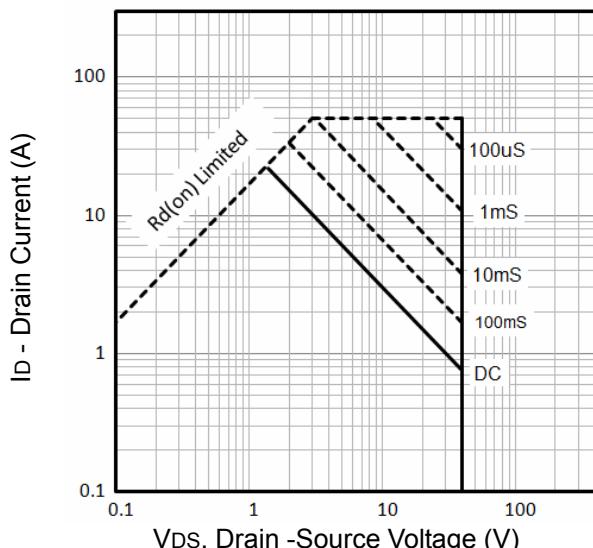
**Fig5.** Typical Source-Drain Diode Forward Voltage



**Fig2.** Threshold Voltage Vs. Temperature



**Fig4.** Normalized On-Resistance Vs. Temperature



**Fig6.** Maximum Safe Operating Area

### Typical Characteristics

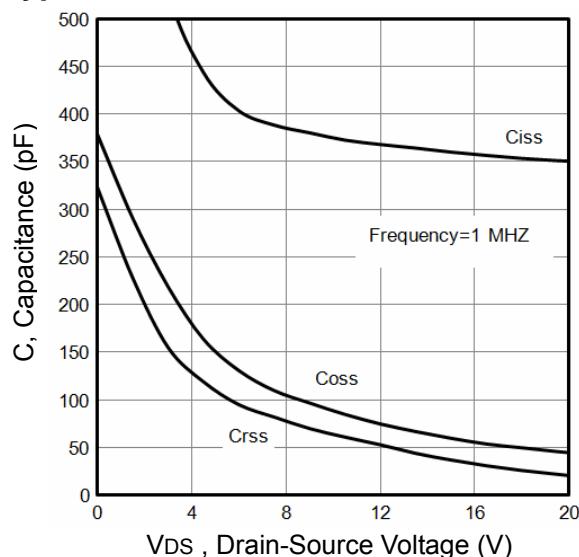


Fig7. Typical Capacitance Vs.Drain-Source Voltage

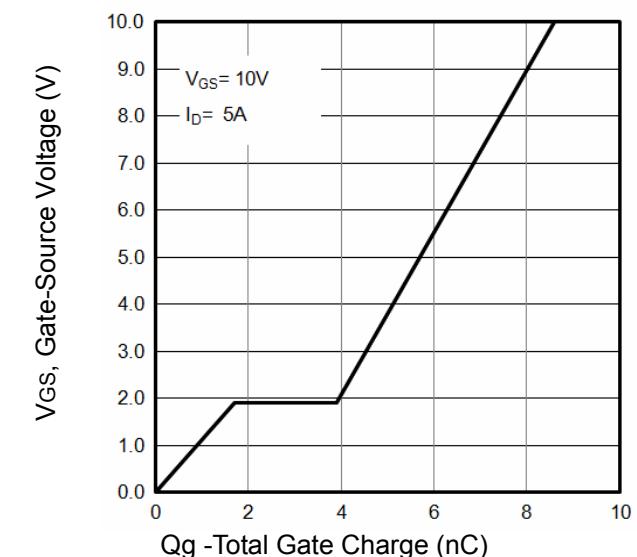
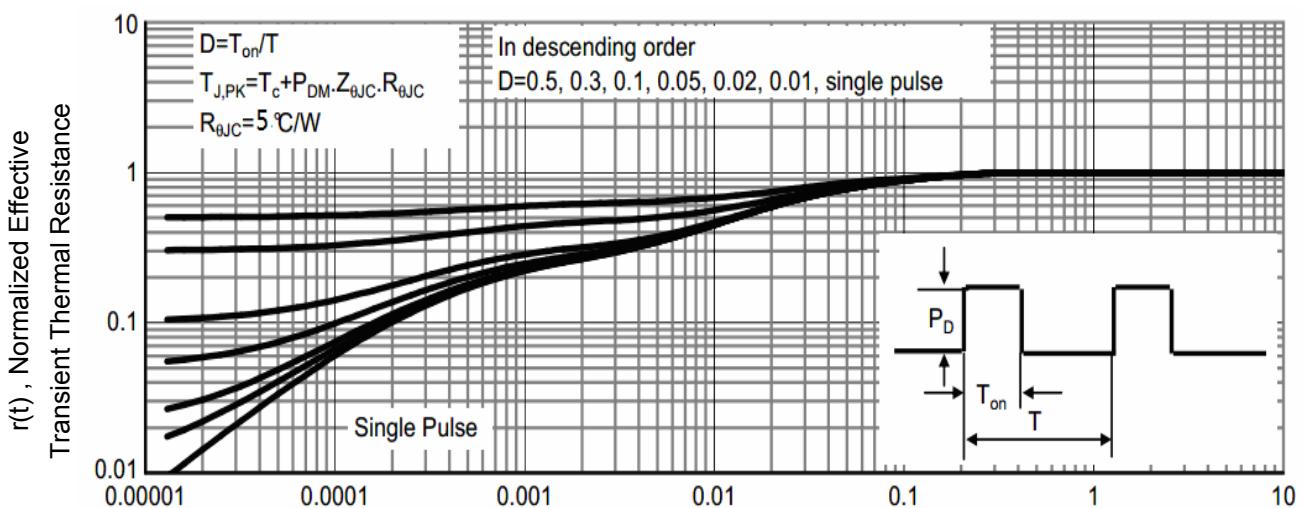


Fig8. Typical Gate Charge Vs.Gate-Source Voltage



T1, Square Wave Pulse Duration(sec)

Fig9. T1 ,Transient Thermal Response Curve

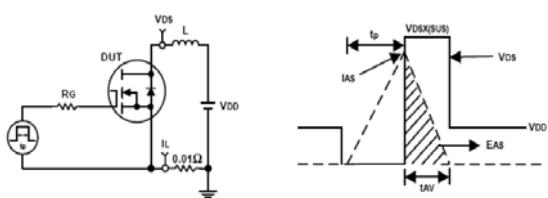


Fig10. Unclamped Inductive Test Circuit and waveforms

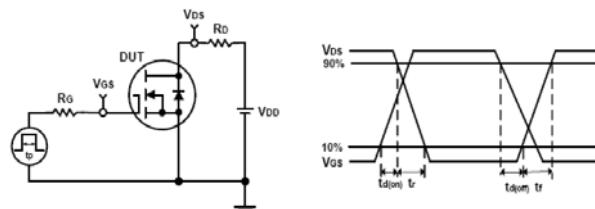
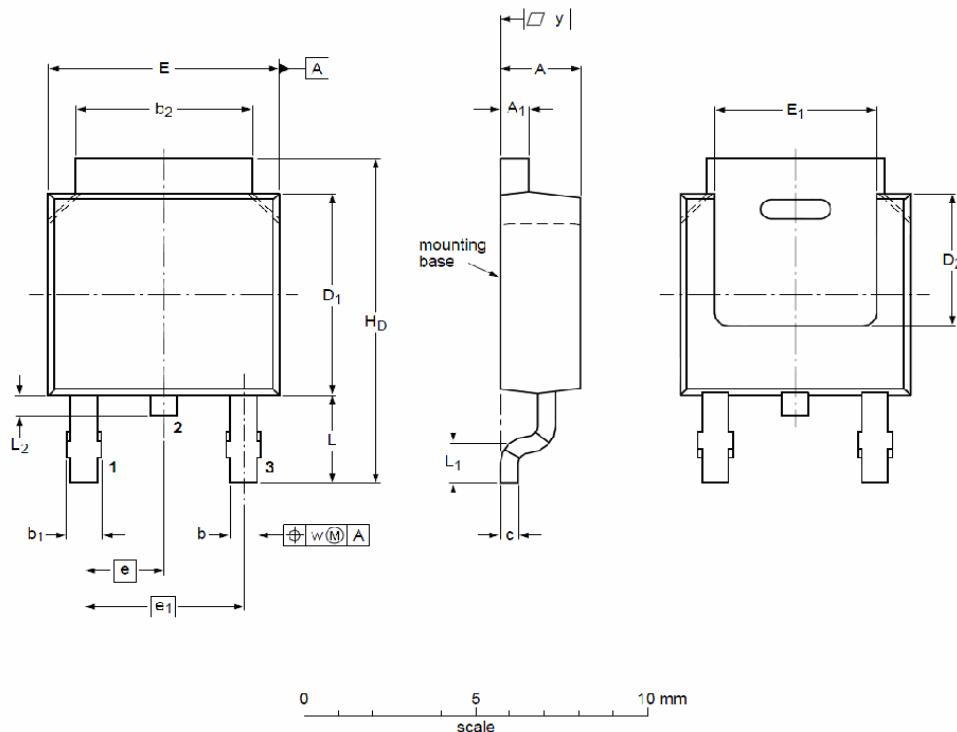


Fig11. Switching Time Test Circuit and waveforms

## TO-252 Package Outline



**DIMENSIONS ( unit : mm )**

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.22	2.30	2.38	A <sub>1</sub>	0.46	0.58	0.93
b	0.71	0.79	0.89	b <sub>1</sub>	0.90	0.98	1.10
b <sub>2</sub>	5.00	5.30	5.46	c	0.20	0.40	0.56
D <sub>1</sub>	5.98	6.05	6.22	D <sub>2</sub>	--	4.00	--
E	6.47	6.60	6.73	E <sub>1</sub>	5.10	5.28	5.45
e	--	2.28	--	e <sub>1</sub>	--	4.57	--
H <sub>b</sub>	9.60	10.08	10.40	L	2.75	2.95	3.05
L <sub>1</sub>	--	0.50	--	L <sub>2</sub>	0.80	0.90	1.10
w	--	0.20	--	y	0.20	--	--

## Customer Service

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